

MATERIALS RESEARCH SOCIETY
SYMPOSIUM PROCEEDINGS VOLUME 917

Gate Stack Scaling: Materials, Role of Interfaces And Reliability Implications

April 17 – 21, 2006
San Francisco, California, USA

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Curran Associates, Inc.
57 Morehouse Lane
Red Hook, NY 12571
www.proceedings.com

ISBN: 978-1-55899-874-2

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CAMBRIDGE UNIVERSITY PRESS
Cambridge, New York, Melbourne, Madrid, Cape Town,
Singapore, São Paulo, Delhi, Tokyo, Mexico City

Cambridge University Press
32 Avenue of the Americas, New York, NY 10013-2473, USA

www.cambridge.org

Materials Research Society
506 Keystone Drive, Warrendale, PA 15086
<http://www.mrs.org>

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First published 2028

CODEN: MRSPDH

ISBN: ; 9: /3/77: ; ; /: 96/4

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